

Publications/Services Standards Conferences Careers/Jobs

Welcome United States Patent and Trademark Office

Help FAQ Terms IEEE Peer Review

Quick Links

» Search Resul

Welcome to IEEE Xplore

- O- Home
- O- What Can | Access?
- O- Log-out

Tables of Contents

- Journals & Magazines
-)- Conference Proceedings
- Standards

Search

- O- By Author
- O- Basic
- O- Advanced

Member Services

- O Join IEEE
- Establish IEEE Web Account
- Print Format

Your search matched 18 of 764280 documents.

Results are shown 25 to a page, sorted by publication year in descending order.

You may refine your search by editing the current search expression or entering a new one the text box.

Then click Search Again.

(dc stress) and (ac stress) and (hot carrier)

Search Again

Results:

Journal or Magazine = JNL Conference = CNF Standard = STD

1 Deuterium isotope effect for AC and DC hot-carrier degradation of MOS transistors: a comparison study

Zhi Chen; Kangguo Cheng; Jinju Lee; Lyding, J.W.; Hess, K.; Chetlur, S. Electron Devices, IEEE Transactions on , Volume: 48 Issue: 4 , April 2001

Page(s): 813 -815

[Abstract] [PDF Full-Text (88 KB)] JNL

2 Latent damage investigation on lateral nonuniform charge generation and stress-induced leakage current in silicon dioxide subjected to high-field current impulse stressing

Wai-Kim Chim; Peng-Soon Lim

Electron Devices, IEEE Transactions on , Volume: 47 Issue: 2 , Feb. 2000

Page(s): 473 -481

[Abstract] [PDF Full-Text (236 KB)] JNL

3 Hot-carrier damage in AC-stressed deep submicrometer CMOS technologies

Bravaix, A.; Goguenheim, D.; Revil, N.; Vincent, E.

Integrated Reliability Workshop Final Report, 1999. IEEE International, 1999

Page(s): 61 -65

[Abstract] [PDF Full-Text (224 KB)] CNF

4 A simple method to estimate lifetime of NMOSFET's in the circuits using DC stress data

Electron Devices, IEEE Transactions on , Volume: 42 Issue: 6 , June 1995

Page(s): 1193 -1195

[Abstract] [PDF Full-Text (256 KB)] JNL

5 Effects of AC hot carrier stress on n- and p-MOSFET's with oxynitride gate dielectrics

Joshi, A.B.; Kwong, D.L.

Electron Devices, IEEE Transactions on , Volume: 41 Issue: 5 , May 1994

Page(s): 671 -674

[Abstract] [PDF Full-Text (396 KB)] JNL

6 AC versus DC hot-carrier degradation in n-channel MOSFETs Mistry, K.R.; Doyle, B.

Electron Devices, IEEE Transactions on , Volume: 40 Issue: 1 , Jan. 1993

Page(s): 96 -104

[Abstract] [PDF Full-Text (764 KB)] JNL

7 Tunneling and thermal emission of electrons from a distribution of deep traps in SiO/sub 2/ (nMOSFET)

Hwang, N.; Or, B.S.S.; Forbes, L.

Electron Devices, IEEE Transactions on , Volume: 40 Issue: 6 , June 1993

Page(s): 1100 -1103

[Abstract] [PDF Full-Text (328 KB)] JNL

8 Mechanisms for hot-carrier-induced degradation in reoxidized-nitrided-oxide n-MOSFET's under combined AC/DC stressing

Ma, Z.-J.; Lai, P.T.; Liu, Z.H.; Ko, P.K.; Cheng, Y.C.

Electron Devices, IEEE Transactions on , Volume: 40 Issue: 6 , June 1993

Page(s): 1112 -1120

[Abstract] [PDF Full-Text (900 KB)] JNL

9 AC hot-carrier degradation in a voltage controlled oscillator

Jiang, C.; Johnson, E.; Shaw, J.J.; Hu, C.

Reliability Physics Symposium, 1993. 31st Annual Proceedings., International , 1993

Page(s): 53 -56

[Abstract] [PDF Full-Text (192 KB)] CNF

10 Hot-carrier-induced degradation in reoxidized-nitrided-oxide n-MOSFETs under mixed AC-DC stressing

Ma, Z.J.; Lai, P.T.; Cheng, Y.C.

IEEE Electron Device Letters , Volume: 13 Issue: 6 , June 1992

Page(s): 314 -316

[Abstract] [PDF Full-Text (236 KB)] JNL

11 A new model on the mechanisms of high-frequency AC hot-carrier effects in MOS devices

Chung-Yu Wu; Charng-Feng Hsu; Ying-Che Wu

VLSI Technology, Systems, and Applications, 1991. Proceedings of Technical Papers, 1991 International

Symposium on , 1991

Page(s): 288 -292

[Abstract] [PDF Full-Text (348 KB)] CNF

12 The role of electron trap creation in enhanced hot-carrier degradation during AC stress (n-channel MOSFET)

Mistry, K.; Doyle, B.

IEEE Electron Device Letters , Volume: 11 Issue: 6 , June 1990

Page(s): 267 -269

[Abstract] [PDF Full-Text (232 KB)] JNL

13 AC/DC characterization of NMOS and PMOS hot-carrier-induced degradation under AC/DC stress

Dawes, M.; Alavi, M.; Kim, D.M.

Electron Devices, IEEE Transactions on , Volume: 37 Issue: 11 , Nov. 1990

Page(s): 2416 -2419

[Abstract] [PDF Full-Text (360 KB)] JNL

14 Direct measurement of hot-carrier stress effects on CMOS circuit performance

Hu, S.C.; Brassington, M.P.

Electron Devices, IEEE Transactions on , Volume: 36 Issue: 11 Part: 2 , Nov. 1989

Page(s): 2604 -2605

[Abstract] [PDF Full-Text (252 KB)] JNL

15 p-MOSFET gate current and device degradation

Ong, T.-C.; Seki, K.; Ko, P.K.; Hu, C.

Reliability Physics Symposium, 1989. 27th Annual Proceedings., International , 1989

Page(s): 178 -182

[Abstract] [PDF Full-Text (392 KB)] CNF

16 Transient hot-electron effect on n-channel device degradation (MOSFETs)

Wang, H.; Davis, M.; De, H.; Bibyk, S.; Nissan-Cohen, Y.

Electron Devices Meeting, 1989. Technical Digest., International, 1989

Page(s): 79 -82

[Abstract] [PDF Full-Text (276 KB)] CNF

17 P-MOSFET gate current and device degradation

Ong, T.-C.; Seki, K.; Ko, P.K.; Hu, C.

VLSI Technology, Systems and Applications, 1989. Proceedings of Technical Papers. 1989 International

Symposium on , 1989

Page(s): 193 -196

[Abstract] [PDF Full-Text (288 KB)] CNF

18 Hot-carrier-induced degradation in p-MOSFETs under AC stress

Ong, T.-C.; Seki, K.; Ko, P.K.; Hu, C.

IEEE Electron Device Letters , Volume: 9 Issue: 5 , May 1988

Page(s): 211 -213

[Abstract] [PDF Full-Text (180 KB)] JNL

Home | Log-out | Journals | Conference Proceedings | Standards | Search by Author | Basic Search | Advanced Search Join IEEE | Web Account | New this week | OPAC Linking Information | Your Feedback | Technical Support | Email Alerting No Robots Piease | Release Notes | IEEE Online Publications | Help. | FAQ | Terms | Back to Top

Copyright © 2002 IEEE - All rights reserved